Abstracts

Model Verification for a High-Power-Efficiency AlGaAs-GaAs HBT

F. Deshours, E. Bergeault, G. Berghoff, C. Pinatel and C. Dubon-Chevallier. "Model Verification for a High-Power-Efficiency AlGaAs-GaAs HBT." 1996 Microwave and Guided Wave Letters 6.1 (Jan. 1996 [MGWL]): 31-33.

Heterojunction bipolar transistors (HBT's) with 2700 μm^2 of emitter area are characterized for model verification using an active load-pull measurement system. The simulation and measurement results (up to 26 dBm) are reported and compared in terms of output power level and power-added efficiency under variable operating conditions. These measurements are performed with the aim of designing power amplifiers for mobile communication.

❑ Return to main document.

Click on title for a complete paper.